

VERSION SHOWING THE CHANGES TO THE SPECIFICATION  
IN THE SUBSTITUTION SPECIFICATION

Page 5, between paragraphs [00021] and [00022], insert a new paragraph as follows:

[00021a] Fig. 1e is a diagrammatic representation of a capacitor according to a further embodiment;

Between paragraphs [00047] and [00048], page 10, insert the following new paragraph:

[00047a] In Fig. 1f, a capacitor according to a further embodiment comprises structure substantially the same as that of the embodiment of Fig. 1b, except there is no insulation layer 4 in the device of Fig. 1f. Parts with the same reference numerals are identical in these figures. The Fig. 1f structure has a top electrode 5 and a bottom electrode 2' as shown in Fig. 1c, mounted on a substrate 1. The semiconductor layer 3' is between the top electrode 5 and bottom electrode 2'. As known, the semiconductor layer acts as an insulator at high frequencies in the MHz and GHz range thus forming the device of Fig. 1f into a capacitor.